

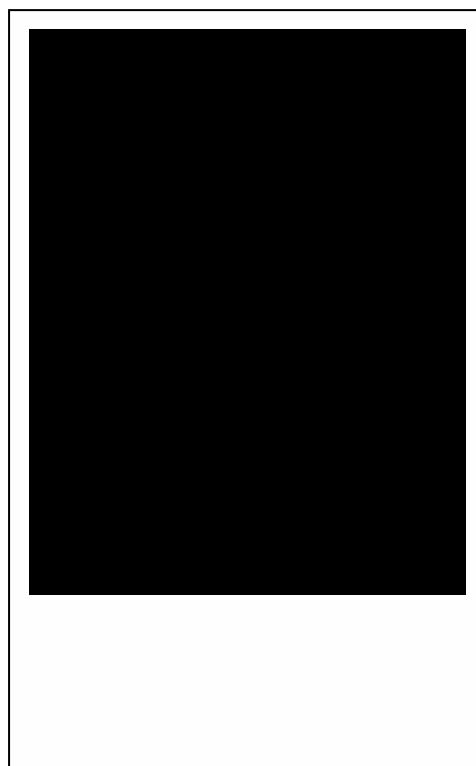


JX075F 12A Sensitive SCR

Rev.A.1.1

DESCRIPTION:

The JX075F SCR provides high dV/dt rate with strong resistance to electromagnetic interface. It is especially recommended for use on residual current circuit breaker, straight hair, igniter etc. From all three terminals to external heatsink, JX075F provides a rated insulation voltage of 2000 V_{RMS} . complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM} / V_{RRM}	800	V
I_{GT}	200	μA

ABSOLUTE MAXIMUM RATINGS

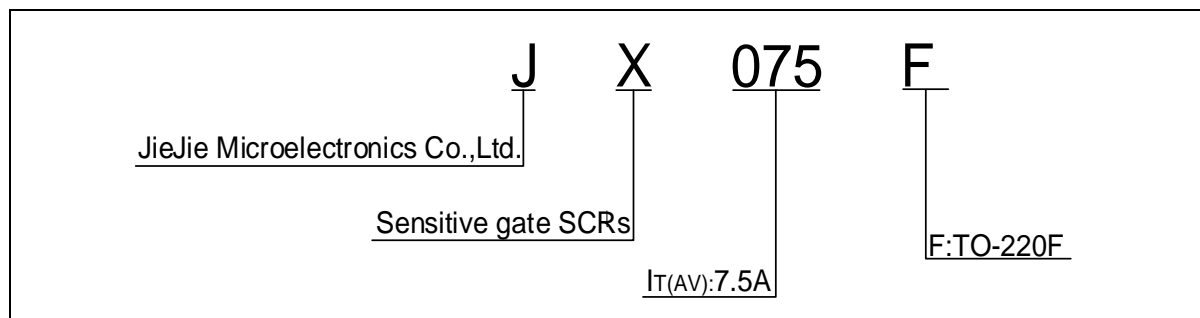
Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-110	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	800	V
Average on-state current ($T_c = 65^\circ C$)	$I_{T(AV)}$	7.5	A
RMS on-state current ($T_c = 65^\circ C$)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^\circ C$)	I_{TSM}	120	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^\circ C$)		130	
I^2t value for fusing ($t_p=10ms, T_j=25^\circ C$)	I^2t	72	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}, f=100Hz, T_j=110^\circ C$)	di/dt	100	$A/\mu s$
Peak gate current ($t_p=20\mu s, T_j=110^\circ C$)	I_{GM}	4	A

Average gate power dissipation ($T_j=110$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	

ORDERING INFORMATION



MARKING

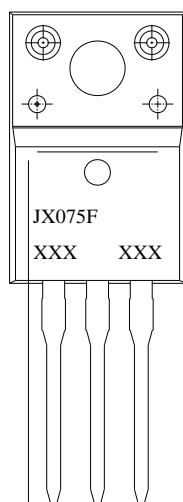


FIG.1: Maximum power dissipation versus RMS on-state current

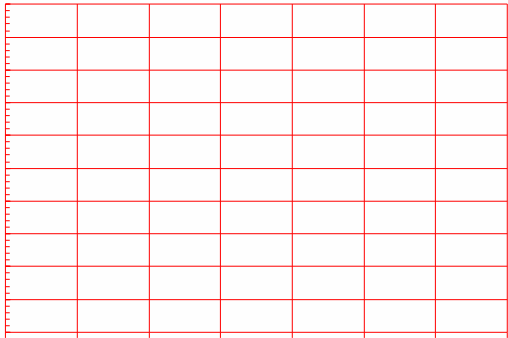



FIG.2: RMS on-state current versus case temperature

ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(μ A)	Package	Base qt
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